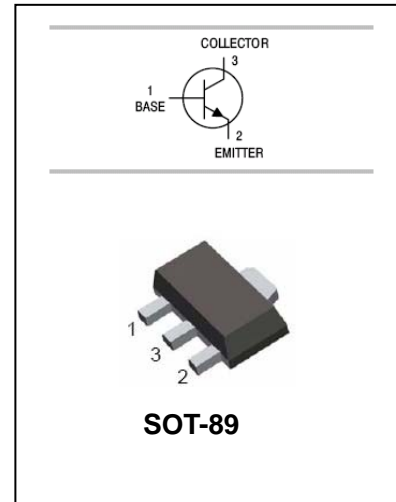


## Power Transistor

## KTD1898

### FEATURES

- High  $V_{CEO}, V_{CEO}=80V$ .
- High  $I_C, I_C=1A(DC)$ .
- Good  $H_{FE}$  Linearity.
- Low  $V_{CE(sat)}$ .
- Complement the 2SB1260.



### APPLICATIONS

- NPN silicon transistor.

### ORDERING INFORMATION

Type No.	Marking	Package Code
KTD1898	DF	SOT-89

### MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	1	A
$I_C$	Collector Current -pulse	2	A
$P_C$	Collector Dissipation	0.5 1	W W
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^{\circ}C$

Note1: Mounted on ceramic substrate(250mm<sup>2</sup>\*0.8t)



**Power Transistor**

**KTD1898**

**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	80			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=80V, I_E=0$			1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4V, I_C=0$			1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=3V, I_C=0.5A$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$			0.4	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=50mA, f=100MHz$		100		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		20		pF

**CLASSIFICATION OF  $h_{FE(1)}$**

Rank	O	Y	R
Range	70-140	120-240	200-400

**TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

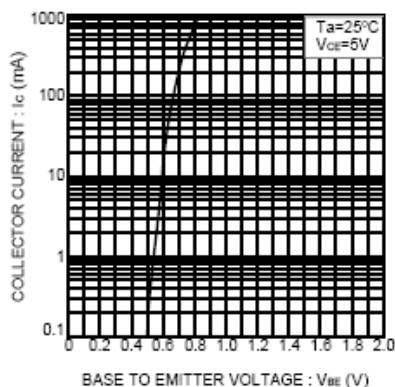


Fig.1 Grounded emitter propagation characteristics

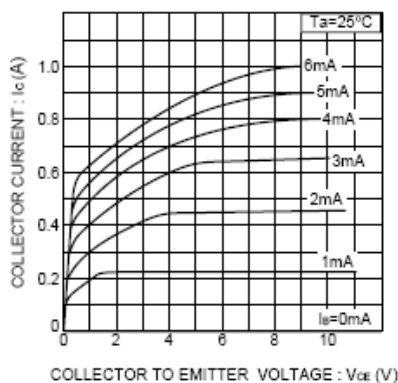


Fig.2 Grounded emitter output characteristics

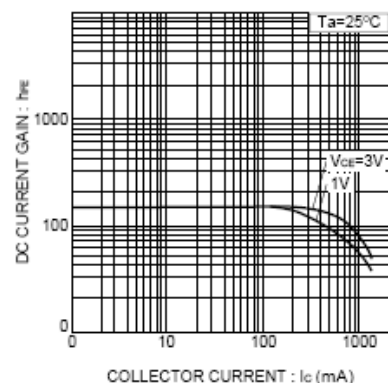


Fig.3 DC current gain vs. collector current

**Power Transistor**

**KTD1898**

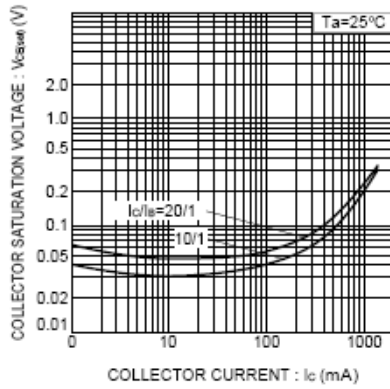


Fig.4 Collector-emitter saturation voltage vs. collector current

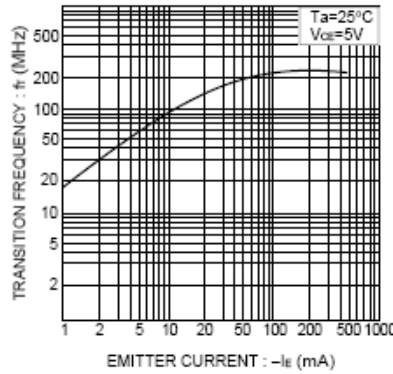


Fig.5 Gain bandwidth product vs. emitter current

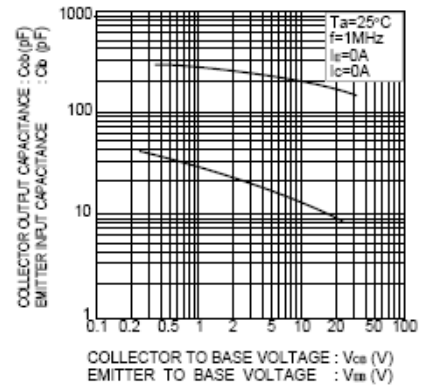


Fig.6 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

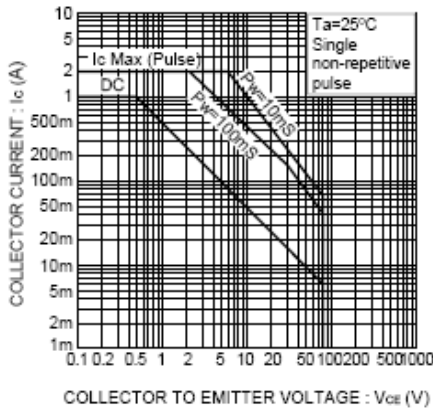


Fig.8 Safe operating area

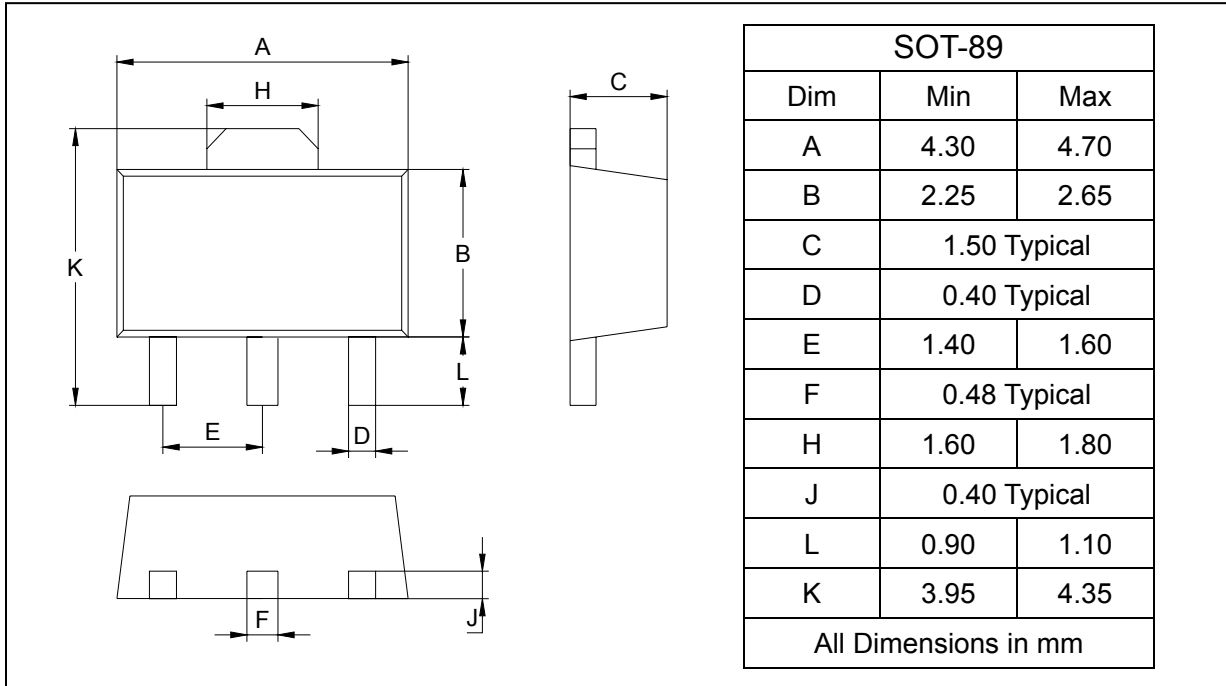
**Power Transistor**

**KTD1898**

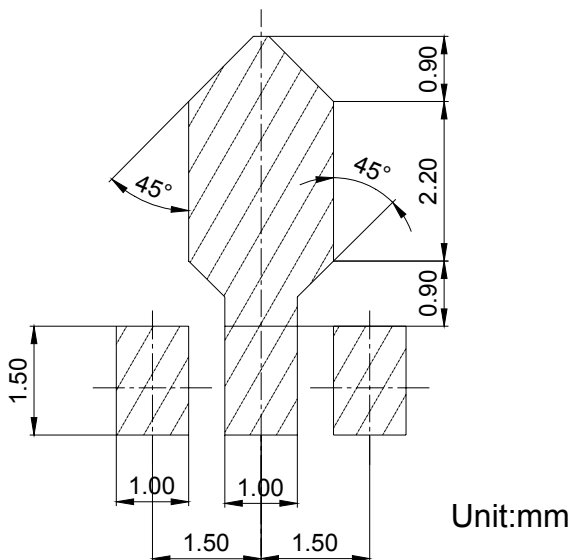
**PACKAGE OUTLINE**

Plastic surface mounted package

SOT-89



**SOLDERING FOOTPRINT**



**PACKAGE INFORMATION**

Device	Package	Shipping
KTD1898	SOT-89	1000/Tape&Reel